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**REPLY UNDER 37 CFR 1.116  
EXPEDITED PROCEDURE  
TECHNOLOGY CENTER 2800**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

**Serial No.:** 10/709,776

**Conf. No.:** 3775

**Filing Date:** 05/27/2004

**Art Unit:** 2811

**Applicant:** William G. America

**Examiner:** Im, Junghwa M.

**Title:** SEMICONDUCTOR DEVICE  
FORMED BY IN-SITU MODIFICATION  
OF DIELECTRIC LAYER AND  
RELATED METHODS

**Docket No.:** FIS920040083US1  
(IBMF-0058)

**COMMISSIONER FOR PATENTS**

**DESTINATION FACSIMILE NUMBER:** 571-273-8300

Transmitted herewith is:

**After-Final Amendment in 09 pages**

in the above identified application.

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In Re Application of: William G. America

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Examiner: Im, Junghwa M

Mail Stop AF  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

## AFTER-FINAL AMENDMENT

Sir:

## I. INTRODUCTORY COMMENTS

This paper is being filed in response to the Final Office Action dated June 05, 2006.

Please amend the above-referenced patent application as follows:

10/709,776

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